Silicon NPN Power Transistors BU536

DESCRIPTION

- With TO-3 package
- High voltage
- Fast switching speed

APPLICATIONS

- For color TV horizontal deflection circuits.

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1100	V
V_{CEO}	Collector-emitter voltage	Open base	480	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		8	A
I_{CM}	Collector current-peak	t_p<5ms	15	A
P_T	Total power dissipation	T_C=25℃	62	W
T_j	Junction temperature		175	℃
T_{stg}	Storage temperature		-65~175	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}C}$	Thermal resistance junction to case	1.0	℃/W

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA; I_B=0;	480			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=10mA; I_C=0;	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4A;I_B=0.8A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4A;I_B=0.8A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=1100V;I_E=0			1.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=5V;I_C=0			0.1	mA
h_{FE-1}	DC current gain	I_C=1A ; V_{CE}=5V	10			
h_{FE-2}	DC current gain	I_C=4A ; V_{CE}=5V	5.5			

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PACKAGE OUTLINE

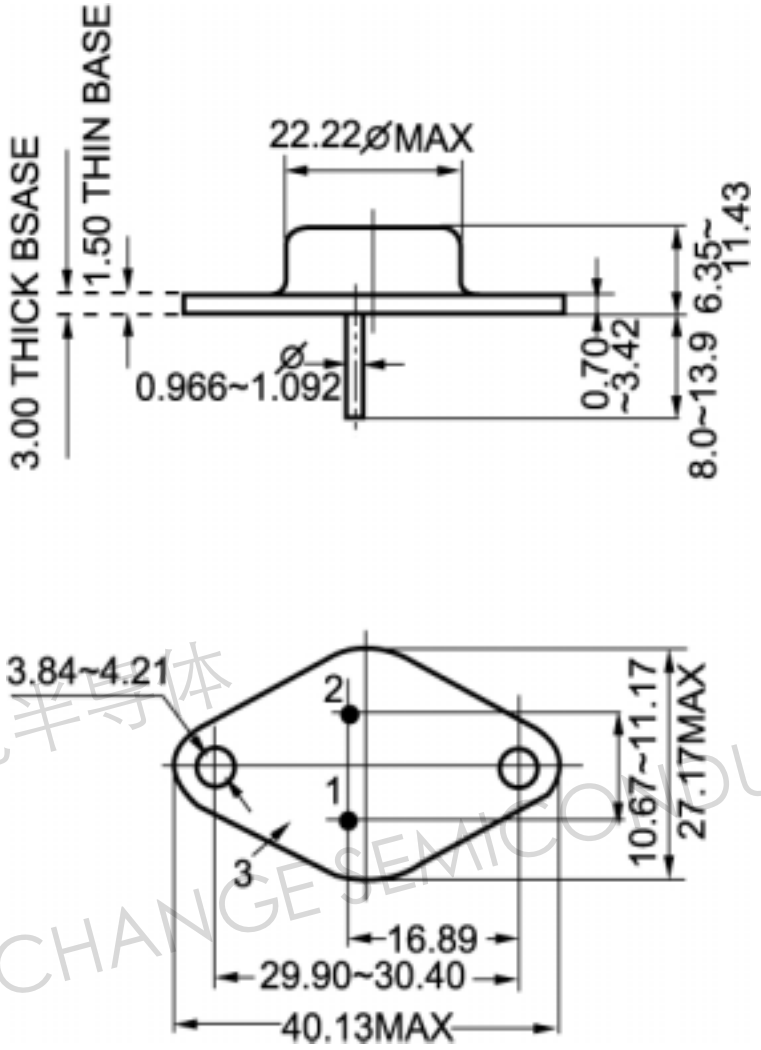

Fig.2 Outline dimensions